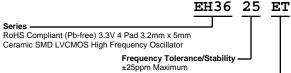
EH3625ETTS-70.656M





TS -70.656M

- Nominal Frequency

70.656MHz

- Pin 1 Connection Tri-State (High Impedance)

Duty Cycle 50 ±10(%)

Operating Tempera	ature Range -
-40°C to +85°C	-

ELECTRICAL SPECIFICATIONS

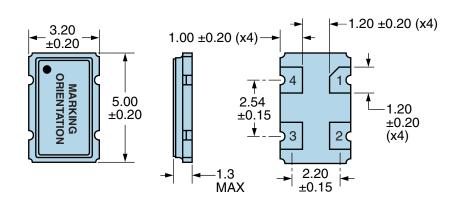
Series -

20 Server Maximum (Inclusive of all conditions) Calibration Talanance at 25% Ensurement Otability such that
±25ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration)
±5ppm/year Maximum
-40°C to +85°C
3.3Vdc ±0.3Vdc
35mA Maximum (No Load)
2.7Vdc Minimum (IOH = -8mA)
0.5Vdc Maximum (IOL = +8mA)
4nSec Maximum (Measured at 20% to 80% of waveform)
50 ±10(%) (Measured at 50% of waveform)
15pF Maximum
CMOS
Tri-State (High Impedance)
70% of Vdd Minimum to enable output, 20% of Vdd Maximum to disable output, No Connect to enable output.
±250pSec Maximum, ±100pSec Typical
±50pSec Maximum, ±40pSec Typical
10mSec Maximum
-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, MEthod 1010
Vibration	MIL-STD-883, Method 2007, Condition A

EH3625ETTS-70.656M

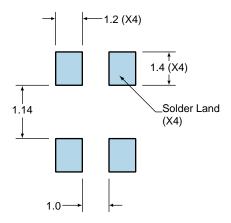
MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage
LINE	MARKING
1	E70.656 <i>E=Ecliptek Designator</i>

Suggested Solder Pad Layout

All Dimensions in Millimeters



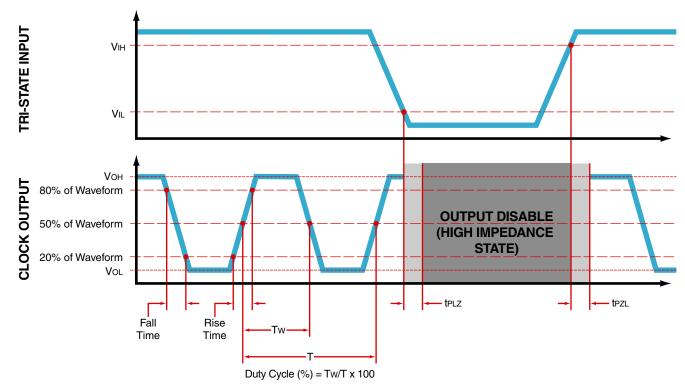
All Tolerances are ±0.1



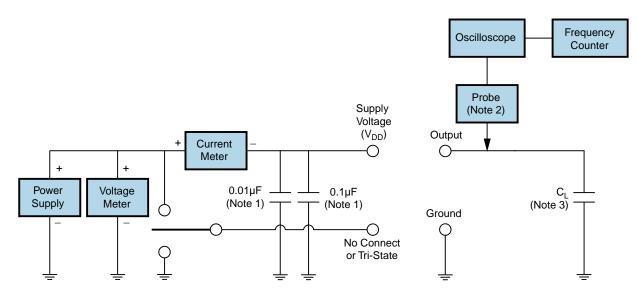
EH3625ETTS-70.656M



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



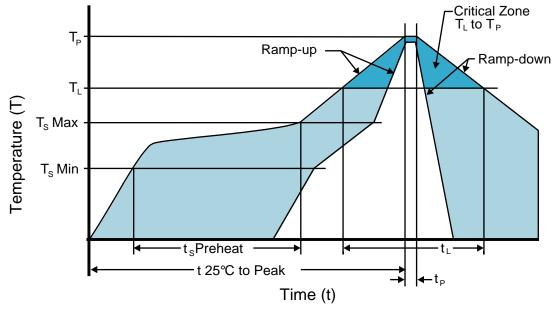
Note 1: An external 0.1μ F low frequency tantalum bypass capacitor in parallel with a 0.01μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

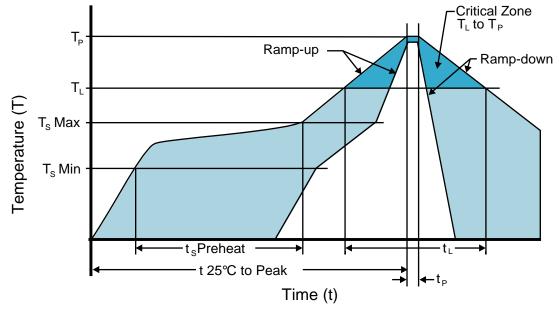
EH3625ETTS-70.656M

T_s MAX to T_L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _P)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1



Recommended Solder Reflow Methods

EH3625ETTS-70.656M



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	te) 5°C/second Maximum	
Preheat		
- Temperature Minimum (T _s MIN)	N/A	
- Temperature Typical (T _s TYP)	150°C	
- Temperature Maximum (T _s MAX)	N/A	
- Time (t _s MIN)	60 - 120 Seconds	
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum	
Time Maintained Above:		
- Temperature (T₋)	150°C	
- Time (t∟)	200 Seconds Maximum	
Peak Temperature (T _P)	240°C Maximum	
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times	
Time within 5°C of actual peak (t _p)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time	
Ramp-down Rate	5°C/second Maximum	
Time 25°C to Peak Temperature (t)	N/A	
Moisture Sensitivity Level	Level 1	

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.